

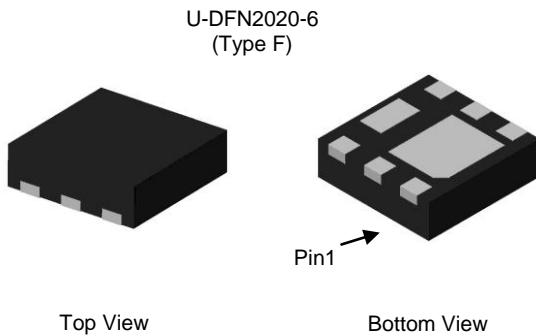
## Product Summary

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> max        | I <sub>D</sub> max<br>T <sub>A</sub> = +25°C |
|-------------------|--------------------------------|----------------------------------------------|
| 30V               | 20.5mΩ @ V <sub>GS</sub> = 10V | 8.3A                                         |
|                   | 30mΩ @ V <sub>GS</sub> = 4.5V  | 7.4A                                         |

## Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

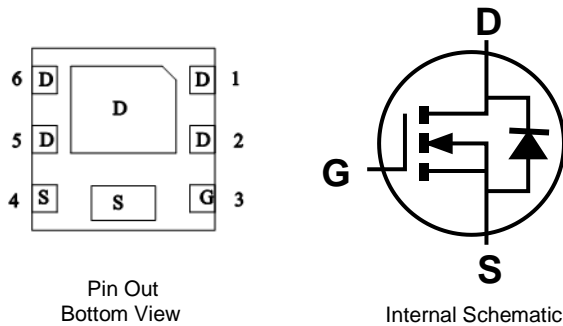


## Features and Benefits

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 [e4](#)
- Weight: 0.0065 grams (Approximate)

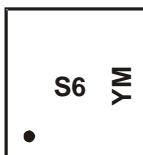


## Ordering Information (Note 4)

| Part Number    | Case                 | Packaging          |
|----------------|----------------------|--------------------|
| DMN3025LFDF-7  | U-DFN2020-6 (Type F) | 3,000/Tape & Reel  |
| DMN3025LFDF-13 | U-DFN2020-6 (Type F) | 10,000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



S6 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: D = 2016)  
 M = Month (ex: 9 = September)

### Date Code Key

| Year | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 |
|------|------|------|------|------|------|------|------|------|
| Code | D    | E    | F    | G    | H    | I    | J    | K    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                          | Symbol                                                           | Value      | Units |
|---------------------------------------------------------|------------------------------------------------------------------|------------|-------|
| Drain-Source Voltage                                    | V <sub>DSS</sub>                                                 | 30         | V     |
| Gate-Source Voltage                                     | V <sub>GSS</sub>                                                 | ±20        | V     |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V | Steady State<br>T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | 8.3<br>6.6 | A     |
|                                                         | t < 10s<br>T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C      | 9.9<br>7.9 | A     |
| Maximum Continuous Body Diode Forward Current (Note 6)  | I <sub>S</sub>                                                   | 3          | A     |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%)      | I <sub>DM</sub>                                                  | 40         | A     |
| Avalanche Current (L = 0.1mH) (Note 7)                  | I <sub>AS</sub>                                                  | 15         | A     |
| Avalanche Energy (L = 0.1mH) (Note 7)                   | E <sub>AS</sub>                                                  | 11         | mJ    |

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                   | Symbol                            | Value                  | Units |
|--------------------------------------------------|-----------------------------------|------------------------|-------|
| Total Power Dissipation (Note 5)                 | P <sub>D</sub>                    | T <sub>A</sub> = +25°C | 0.66  |
|                                                  |                                   | T <sub>A</sub> = +70°C | 0.42  |
| Thermal Resistance, Junction to Ambient (Note 5) | R <sub>θJA</sub>                  | Steady State           | 173   |
|                                                  |                                   | t < 10s                | 133   |
| Total Power Dissipation (Note 6)                 | P <sub>D</sub>                    | T <sub>A</sub> = +25°C | 2.1   |
|                                                  |                                   | T <sub>A</sub> = +70°C | 1.3   |
| Thermal Resistance, Junction to Ambient (Note 6) | R <sub>θJA</sub>                  | Steady State           | 62    |
|                                                  |                                   | t < 10s                | 43    |
| Thermal Resistance, Junction to Case (Note 6)    | R <sub>θJC</sub>                  | 9.4                    | °C/W  |
| Operating and Storage Temperature Range          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150            | °C    |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                             | Symbol              | Min | Typ  | Max  | Unit | Test Condition                                                                            |
|--------------------------------------------|---------------------|-----|------|------|------|-------------------------------------------------------------------------------------------|
| <b>OFF CHARACTERISTICS (Note 8)</b>        |                     |     |      |      |      |                                                                                           |
| Drain-Source Breakdown Voltage             | BV <sub>DSS</sub>   | 30  | -    | -    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA                                              |
| Zero Gate Voltage Drain Current            | I <sub>DSS</sub>    | -   | -    | 1    | µA   | V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V                                               |
| Gate-Source Leakage                        | I <sub>GSS</sub>    | -   | -    | ±100 | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V                                              |
| <b>ON CHARACTERISTICS (Note 8)</b>         |                     |     |      |      |      |                                                                                           |
| Gate Threshold Voltage                     | V <sub>GS(TH)</sub> | 1.0 | -    | 2.0  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA                                |
| Static Drain-Source On-Resistance          | R <sub>DS(ON)</sub> | -   | -    | 20.5 | mΩ   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 7A                                                |
|                                            |                     | -   | -    | 30   |      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7A                                               |
| Diode Forward Voltage                      | V <sub>SD</sub>     | -   | 0.70 | 1.0  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A                                                 |
| <b>DYNAMIC CHARACTERISTICS (Note 9)</b>    |                     |     |      |      |      |                                                                                           |
| Input Capacitance                          | C <sub>ISS</sub>    | -   | 641  | -    | pF   | V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz                                |
| Output Capacitance                         | C <sub>OSS</sub>    | -   | 66   | -    |      |                                                                                           |
| Reverse Transfer Capacitance               | C <sub>RSS</sub>    | -   | 50   | -    |      |                                                                                           |
| Gate Resistance                            | R <sub>g</sub>      | -   | 2.2  | -    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz                                    |
| Total Gate Charge (V <sub>GS</sub> = 4.5V) | Q <sub>g</sub>      | -   | 6    | -    | nC   | V <sub>DS</sub> = 15V, I <sub>D</sub> = 10A                                               |
| Total Gate Charge (V <sub>GS</sub> = 10V)  | Q <sub>g</sub>      | -   | 13.2 | -    |      |                                                                                           |
| Gate-Source Charge                         | Q <sub>gs</sub>     | -   | 1.7  | -    |      |                                                                                           |
| Gate-Drain Charge                          | Q <sub>gd</sub>     | -   | 2.2  | -    |      |                                                                                           |
| Turn-On Delay Time                         | t <sub>D(ON)</sub>  | -   | 3.3  | -    | ns   | V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,<br>R <sub>G</sub> = 6Ω, I <sub>D</sub> = 1A |
| Turn-On Rise Time                          | t <sub>R</sub>      | -   | 4.4  | -    |      |                                                                                           |
| Turn-Off Delay Time                        | t <sub>D(OFF)</sub> | -   | 22.3 | -    |      |                                                                                           |
| Turn-Off Fall Time                         | t <sub>F</sub>      | -   | 5.3  | -    |      |                                                                                           |
| Reverse Recovery Time                      | t <sub>RR</sub>     | -   | 11.4 | -    | ns   | I <sub>F</sub> = 11A, di/dt = 100A/µs                                                     |
| Reverse Recovery Charge                    | Q <sub>RR</sub>     | -   | 8.2  | -    | nC   | I <sub>F</sub> = 11A, di/dt = 100A/µs                                                     |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

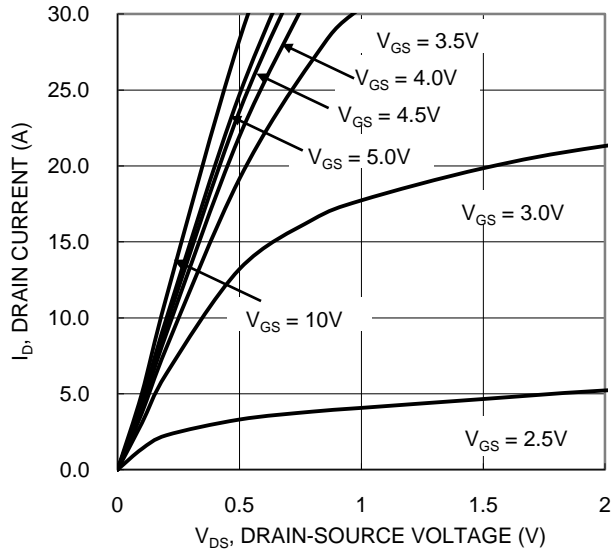


Figure 1. Typical Output Characteristic

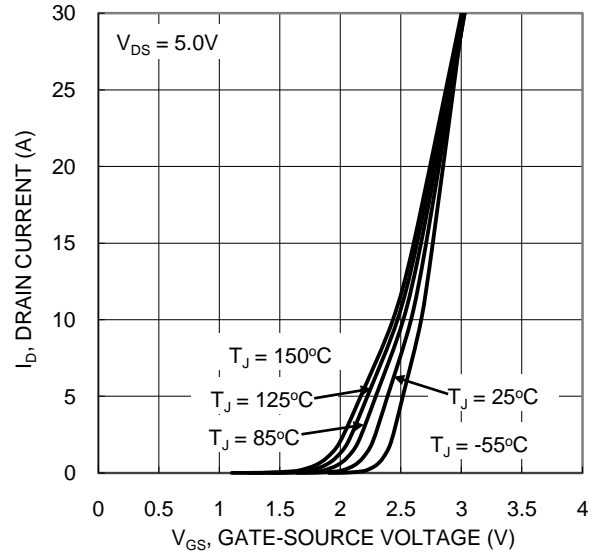


Figure 2. Typical Transfer Characteristic

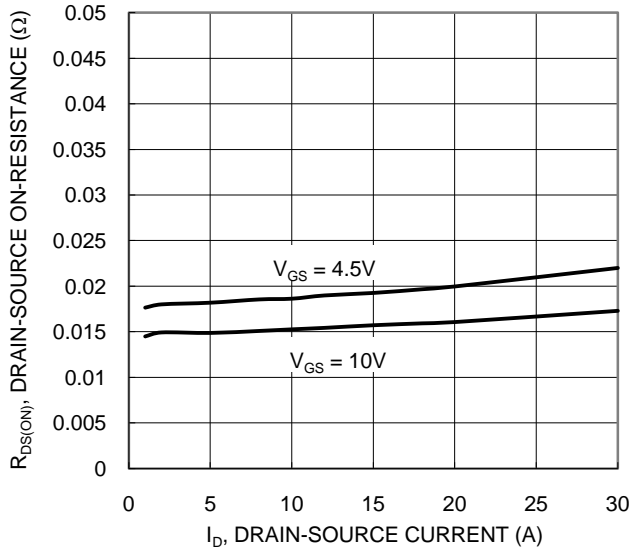


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

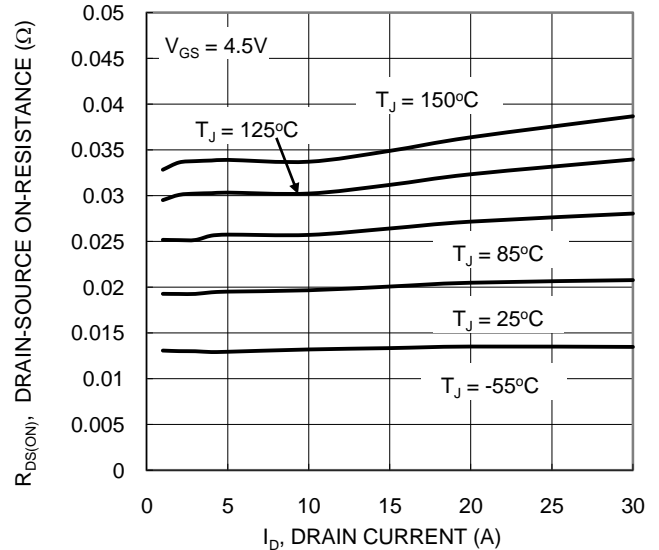


Figure 4. Typical On-Resistance vs Drain Current and Temperature

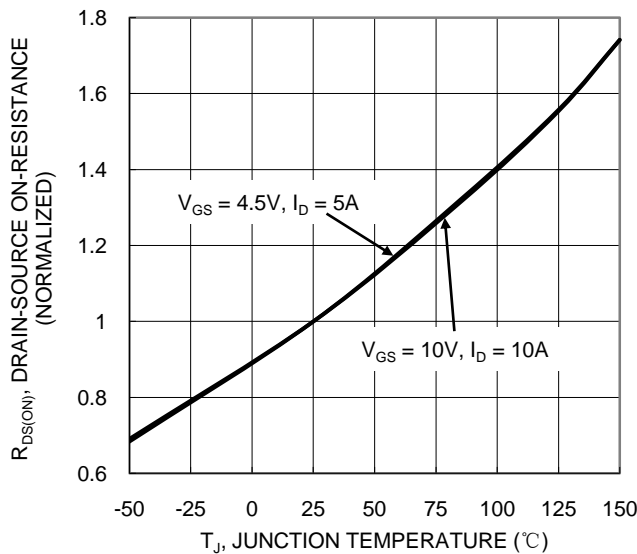


Figure 5. On-Resistance Variation with Temperature

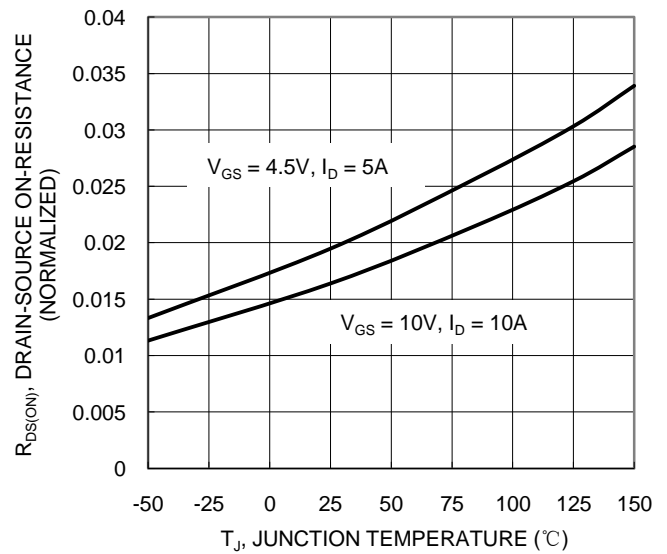


Figure 6. On-Resistance Variation with Temperature

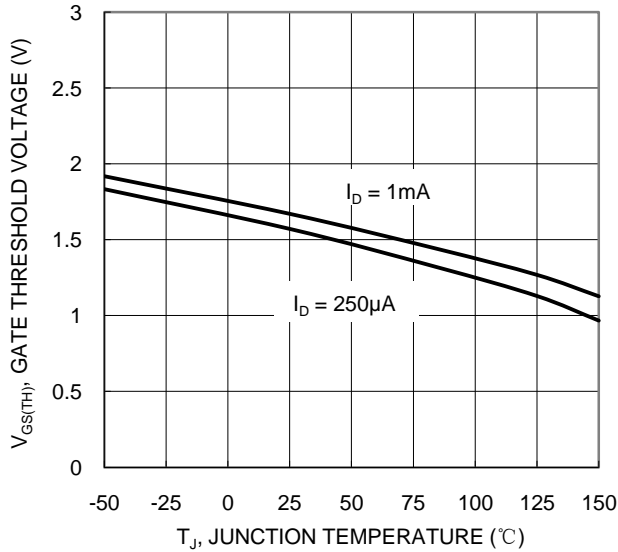


Figure 7. Gate Threshold Variation vs Junction Temperature

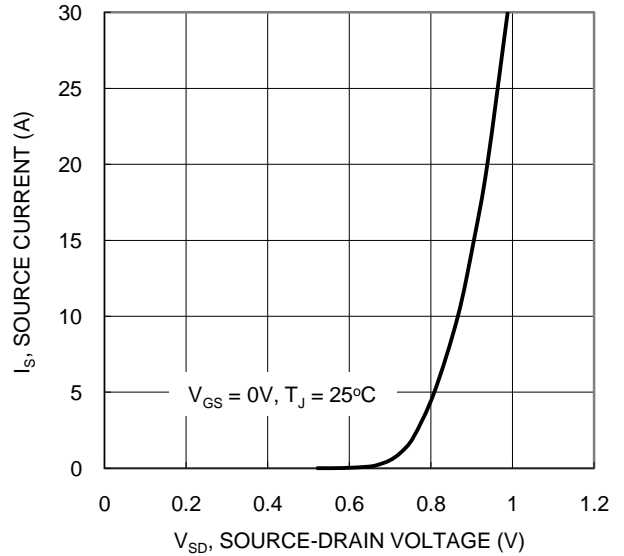


Figure 8. Diode Forward Voltage vs. Current

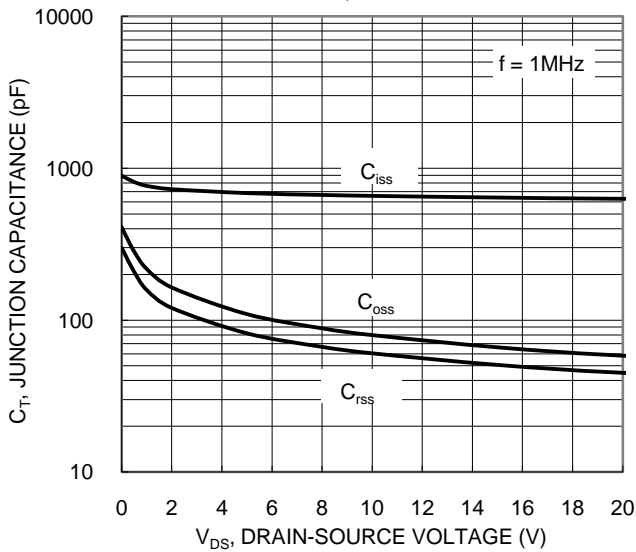


Figure 9. Typical Junction Capacitance

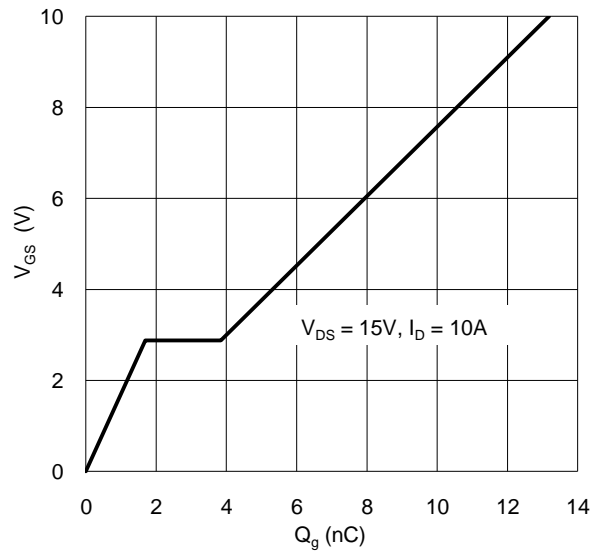


Figure 10. Gate Charge

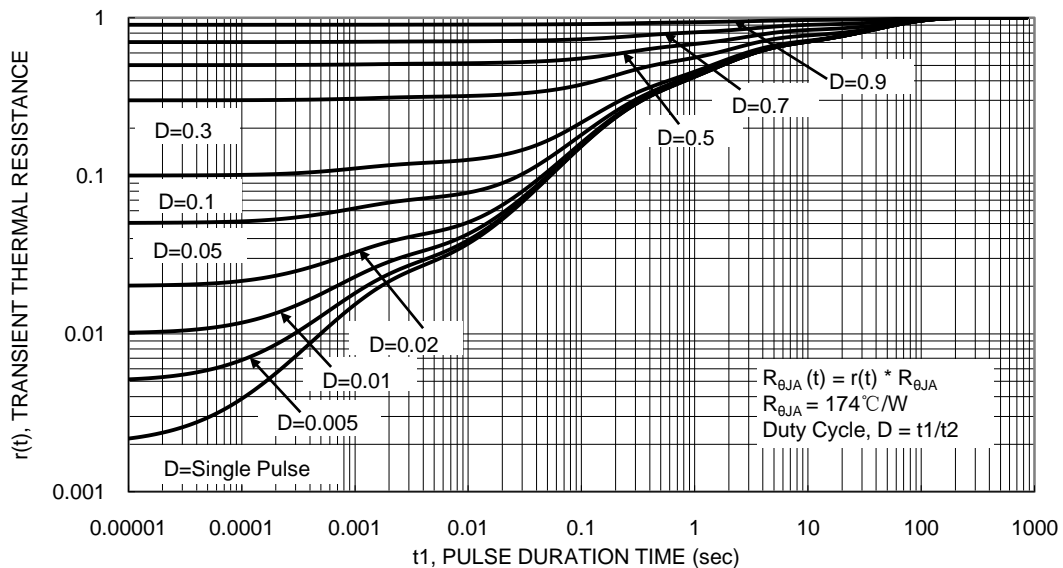
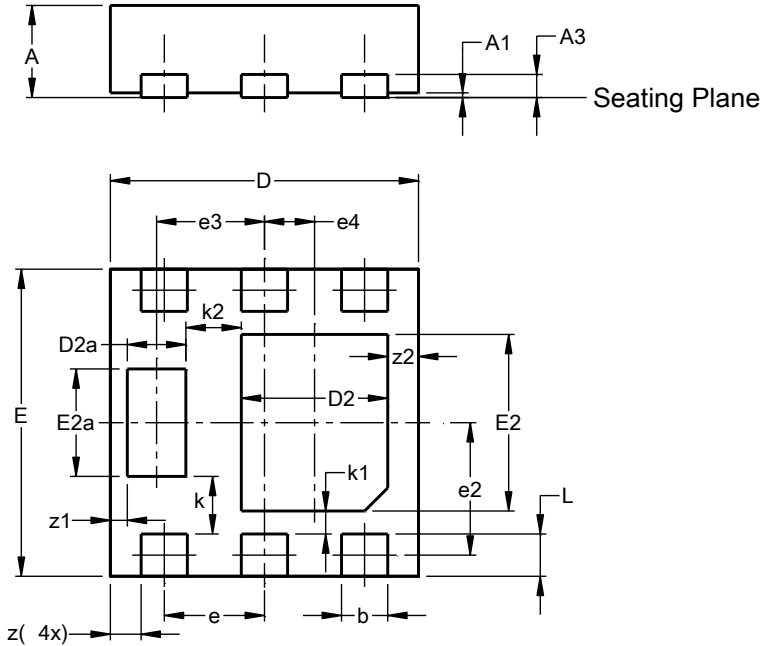


Figure 11. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type F)**

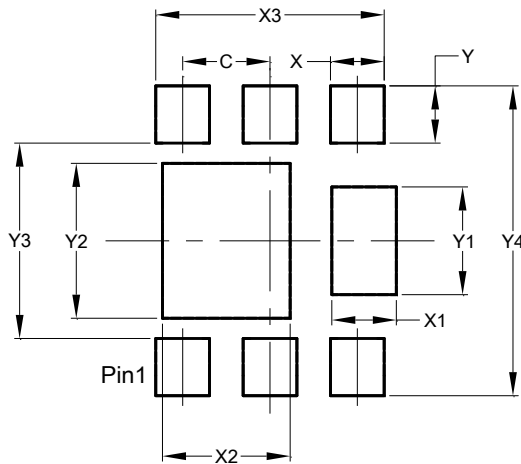


| U-DFN2020-6 (Type F) |           |       |       |
|----------------------|-----------|-------|-------|
| Dim                  | Min       | Max   | Typ   |
| A                    | 0.57      | 0.63  | 0.60  |
| A1                   | 0.00      | 0.05  | 0.03  |
| A3                   | -         | -     | 0.15  |
| b                    | 0.25      | 0.35  | 0.30  |
| D                    | 1.95      | 2.05  | 2.00  |
| D2                   | 0.85      | 1.05  | 0.95  |
| D2a                  | 0.33      | 0.43  | 0.38  |
| E                    | 1.95      | 2.05  | 2.00  |
| E2                   | 1.05      | 1.25  | 1.15  |
| E2a                  | 0.65      | 0.75  | 0.70  |
| e                    | 0.65 BSC  |       |       |
| e2                   | 0.863 BSC |       |       |
| e3                   | 0.70 BSC  |       |       |
| e4                   | 0.325 BSC |       |       |
| k                    | 0.37 BSC  |       |       |
| k1                   | 0.15 BSC  |       |       |
| k2                   | 0.36 BSC  |       |       |
| L                    | 0.225     | 0.325 | 0.275 |
| z                    | 0.20 BSC  |       |       |
| z1                   | 0.110 BSC |       |       |
| z2                   | 0.20 BSC  |       |       |
| All Dimensions in mm |           |       |       |

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type F)**



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 0.650         |
| X          | 0.400         |
| X1         | 0.480         |
| X2         | 0.950         |
| X3         | 1.700         |
| Y          | 0.425         |
| Y1         | 0.800         |
| Y2         | 1.150         |
| Y3         | 1.450         |
| Y4         | 2.300         |

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